Central™
Semiconductor Corp.

PROCESS CPD77

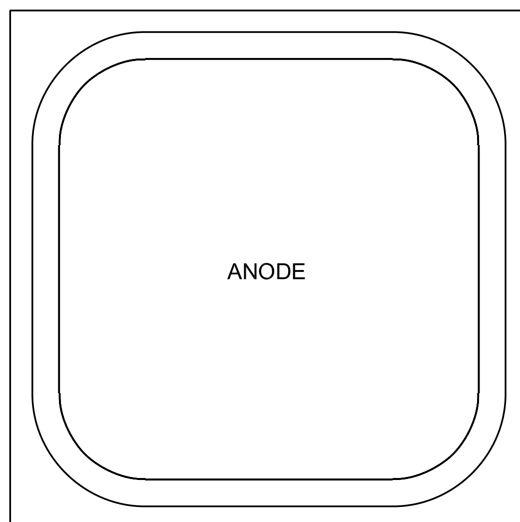
Schottky Rectifier

3.0A Schottky Barrier Rectifier Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	61 x 61 MILS
Die Thickness	9.8 MILS
Anode Bonding Pad Area	55 x 55 MILS
Top Side Metalization	Ti/Ag - (2,500Å/30,000Å)
Back Side Metalization	Ti/Ni/Au - (1,600Å/5,550Å/1,500Å)

GEOMETRY



GROSS DIE PER 4 INCH WAFER
3,118

PRINCIPAL DEVICE TYPES
CTLSH3-30M833

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